# VLSI Week 3

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### 1 Transistor Capacitance

#### 1.1 Gate Capacitance

The gate capacitance is frequently approximated as relative to the ground. The formula for  $C_g s$  is as follows:

$$C_{gs} = \epsilon_{ox} \frac{W}{L} \tag{1}$$

$$C_{gs} = \frac{2}{3}WLC'_{ox} \tag{2}$$

#### 1.2 Diffusion Capacitances

Refer the the capacitance between the source and body, and drain and body. The capacitance between the gate and body can be calculated as:

$$C_{gb} = C'_{ox} L_{eff} W_{drawn} \tag{3}$$

